

版本	修订日期	有修订的页码	修订涉及的内容	拟制	审核
A	2020-6-24			谢小倩	刘晓荣
B	2020-7-9				

/ Descriptions

SOT-363 塑封封装肖特基二极管。

Schottky Diode in a SOT-363 Plastic Package.

/ Features

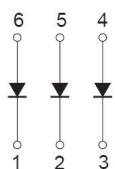
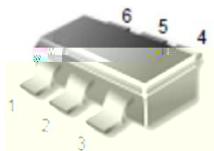
低正向压降，可忽略的反向恢复时间。无卤产品。

Low positive pressure drop, can ignore the reverse recovery time. HF Product.

/ Applications

肖特基二极管。

Schottky diode.

/ Equivalent Circuit**/ Pinning**

PIN: See Equivalent Circuit.

/ h_{FE} Classifications & Marking

Model	SD103ATW
Marking	KLL

/ Absolute Maximum Ratings(Ta=25)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
		SD103ATW	
Peak Repetitive Peak Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	40	V
RMS Reverse Voltage	$V_{R(RMS)}$	28	V
Average Rectified Current	I_O	175	mA
Forward Continuons Current	I_{FM}	350	mA
Non-repetitive Peak Forward Surge Current@t=8.3ms	I_{FSM}	2	A
Power Dissipation	P_D	200	mW
Typical Thermal Resistance Junction to Ambient	$R_{\theta JA}$	500	°C/W
Junction temperature	T_j	125	°C
Junction and Storage Temperature Range	T_{STG}	-55~125	°C

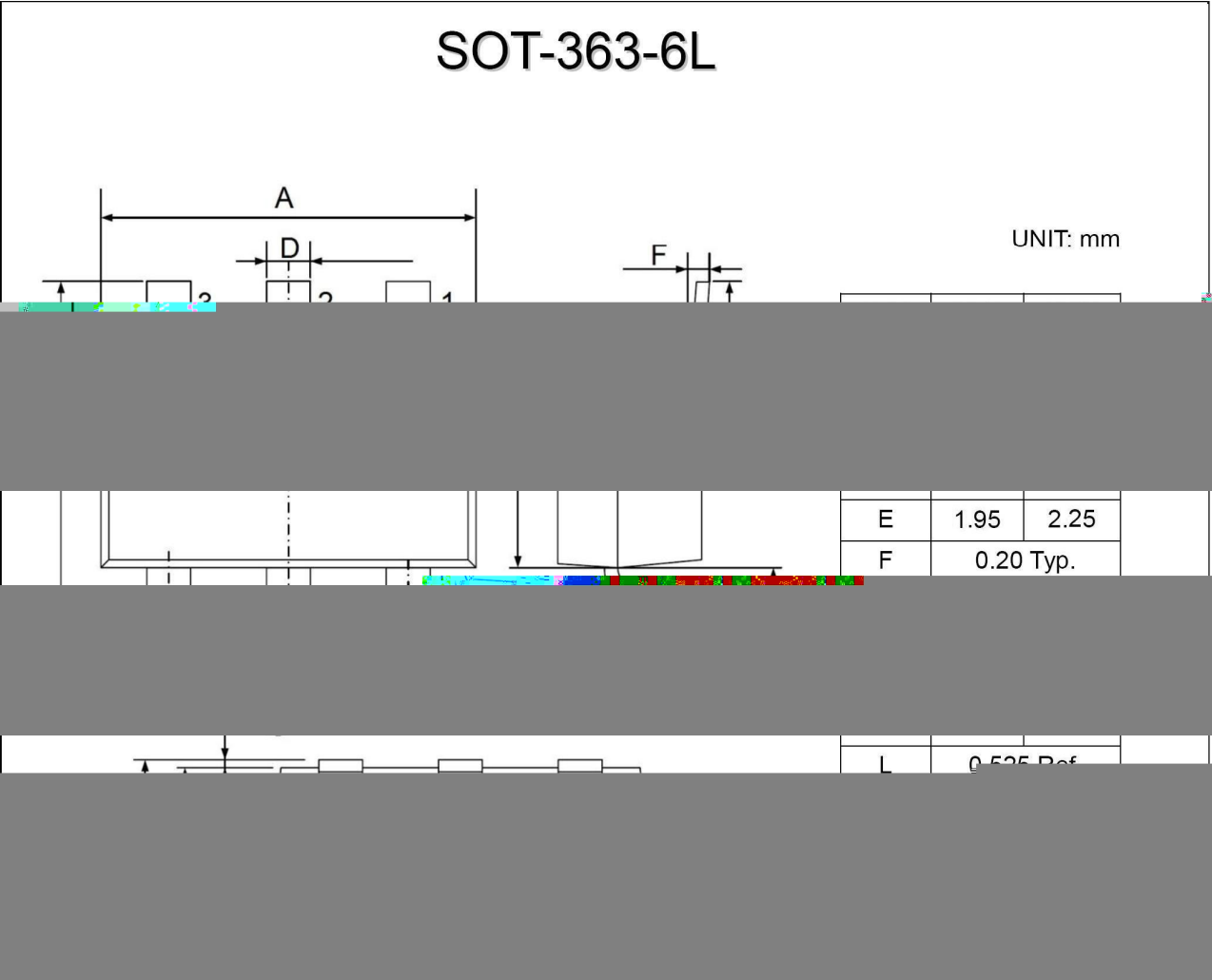
/ Electrical Characteristics(Ta=25)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	40			V
Forward voltage	V_F	$I_F=20mA$			0.37	V
		$I_F=100mA$			0.50	
Reverse current	I_R	$V_R=10V$			2.0	μA
		$V_R=30V$			5.0	
Capacitance between terminals	C_T	$V_R=0V$ $f=1.0MHZ$		50		pF
Resistance Range Time	t_{rr}	$I_F=I_R=200mA$ $I_{rr}=0.1 \times I_R$ $R_L=100\Omega$		10		ns

SD103ATW

Rev.D Oct.-2021

/ Package Dimensions



SD103AT

() / **Temperature Profile for IR Reflow Soldering(Pb-Free)**

Note:

- | | | | |
|---|---------|-----------|--|
| 1 | 150 180 | 60 90sec; | 1.Preheating:150~180°C, Time:60~90sec. |
| 2 | 245±5 | 5±0.5sec; | 2.Peak Temp.:245±5°C, Duration:5±0.5sec. |
| 3 | 2 | 10°C/sec. | 3. Cooling Speed: 2~10°C/sec. |

/ **Resistance to Soldering Heat Test Conditions**

260±5°C	10±1 sec.	Temp.:c	emp.:	I
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